

**AMENDMENTS TO THE CLAIMS**

This listing of claims replaces all prior listing of claims in this application.

Claims 1-25 (Canceled).

26. (Currently amended) ~~A composition suitable for use in etching an insulative layer formed over a substrate in a semiconductor device, said plasma etching composition consisting essentially of:~~

~~a flowing plasma etchant mixture consisting of at least one fluorocarbon two fluorocarbons[[,] and ammonia, wherein said at least one fluorocarbon two fluorocarbons[,] and said ammonia form a reactive mixture.~~

27. (Currently amended) The composition of claim 26, wherein ~~said fluorocarbon is at least one member at least two fluorocarbons are~~ selected from the group consisting of fluorohydrocarbons, chlorofluorocarbons and chlorofluorohydrocarbons.

28. (Currently amended) The composition of claim 27, wherein ~~said fluorocarbon is at least one member at least two fluorocarbons are~~ selected from the group consisting of C<sub>4</sub>F<sub>8</sub>, C<sub>4</sub>F<sub>6</sub>, C<sub>5</sub>F<sub>8</sub>, CF<sub>4</sub>, C<sub>2</sub>F<sub>6</sub>, C<sub>3</sub>F<sub>8</sub>, CHF<sub>3</sub>, and CH<sub>2</sub>F<sub>2</sub>.

29. (Currently amended) The composition of claim 26, wherein ~~said fluorocarbon is at least one member at least two fluorocarbons are~~ selected from the group consisting of CF<sub>4</sub>, CHF<sub>3</sub>, and CH<sub>2</sub>F<sub>2</sub>.

30. (Canceled).

